

### **KSC1187**

# TV 1st, 2nd Picture IF Amplifier (Forward AGC)

High Current Gain Bandwidth Product : f<sub>T</sub>=700MHz
High Power Gain : G<sub>PE</sub>=24dB (TYP.) at f=45MHz



1. Emitter 2. Base 3. Collector

## **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	20	V
V <sub>EBO</sub>	Emitter-Base Voltage	4	V
I <sub>C</sub>	Collector Current	30	mA
P <sub>C</sub>	Collector Power Dissipation	250	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=10\mu A, I_{E}=0$	30			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C=5mA$ , $I_B=0$	25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E}=10\mu A, I_{C}=0$	4			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =20V, I <sub>E</sub> =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =10V, I <sub>C</sub> =2mA	40		240	
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =3mA	400	700		MHz
C <sub>RE</sub>	Reverse Transfer Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		0.6		pF
G <sub>PE</sub>	Power Gain	V <sub>CE</sub> =10V, I <sub>C</sub> =3mA f=45MHz	20	24		dB
V <sub>AGC</sub>	AGC Voltage	G <sub>R</sub> = 30dB, f=45MHz	4.4	5.2	6.0	V

# **h**<sub>FE</sub> Classification

Classification	R	0	Υ
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240

# **Typical Characteristics**

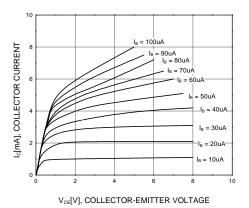
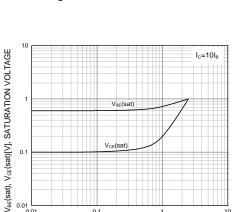


Figure 1. Static Characteristic



I<sub>C</sub>[mA], COLLECTOR CURRENT

Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

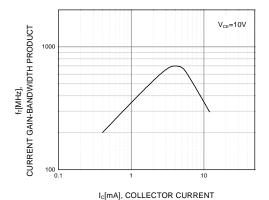


Figure 5. Current Gain Bandwidth Product

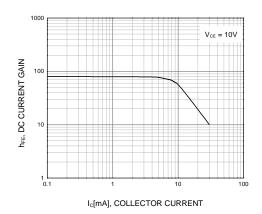


Figure 2. DC current Gain

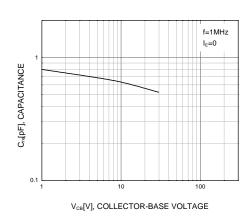
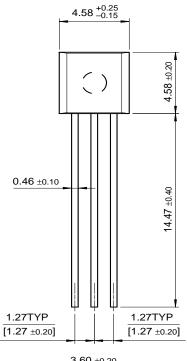


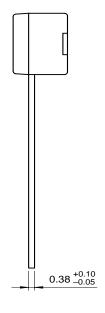
Figure 4. Reverse Capacitance

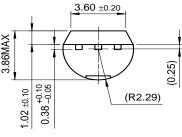
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# **Package Demensions**

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